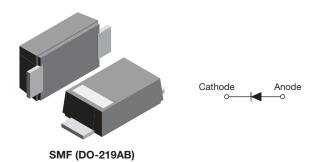
Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt[®]



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| PRODUCT SUMMARY | | | | |
|----------------------------------|----------------|--|--|--|
| Package | DO-219AB (SMF) | | | |
| I _{F(AV)} | 1 A | | | |
| V _R | 100 V | | | |
| V _F at I _F | 0.93 V | | | |
| t _{rr} | 25 ns | | | |
| T _J max. | 175 °C | | | |
| Diode variation | Single die | | | |

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|--|------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Peak repetitive reverse voltage | V _{RRM} | | 100 | V |
| Average rectified forward current | I _{F(AV)} | $T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$ | 1 | ٨ |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 40 | A |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to 175 | °C |

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

| ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified) | | | | | | |
|--|---|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 100 | - | - | |
| Forward voltage | ward voltage V _F | I _F = 1 A | - | 0.87 | 0.93 | V |
| | I _F = 1 A, T _J = 125 °C | - | 0.74 | 0.8 | | |
| Reverse leakage current | I _R | $V_{R} = V_{R}$ rated | - | - | 2 | |
| | | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | 0.5 | 8 | μA |
| Junction capacitance | CT | V _R = 100 V | - | 5 | - | pF |

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(Pb)

ROHS COMPLIANT

HALOGEN

FREE



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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified) | | | | | | | |
|---|--|--|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | I_F = 1.0 A, d I_F /dt = 50 A/µs, V_R = 30 V | | - | 26 | - | | |
| | + | I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A | | - | - | 25 | |
| Reverse recovery time | erse recovery time t _{rr} | T _J = 25 °C | | - | 16 | - | ns |
| | T _J = 125 °C | $I_F = 1 A$ | - | 23 | - | | |
| Peak recovery current I _{RRM} | T _J = 25 °C | | - | 1.6 | - | А | |
| | IRRM | T _J = 125 °C | dI _F /dt = 200 A/μs V _R = 160 V | - | 2.5 | - | A |
| Reverse recovery charge Q _{rr} | 0 | T _J = 25 °C | | - | 13 | - | nC |
| | T _J = 125 °C | | - | 30 | - | 10 | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|---|--------|-------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C |
| Thermal resistance, junction to case | R _{thJC} | Device mounted on PCB with 8 mm x 16 mm soldering lands | - | - | 17 | °C AN |
| Thermal resistance, junction to ambient | R _{thJA} | Device mounted on PCB with 2 mm x 3.5 mm soldering lands | - | - | 140 | °C/W |
| A | | | | 0.015 | | g |
| Approximate weight | | | 0.0005 | | oz. | |
| Marking device | | Case style SMF (DO-219AB) | | А | Ή | |

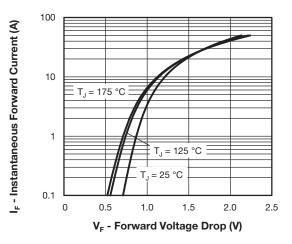
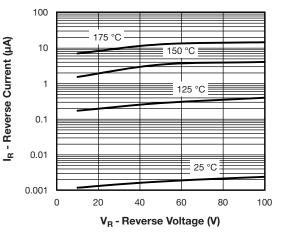
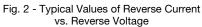
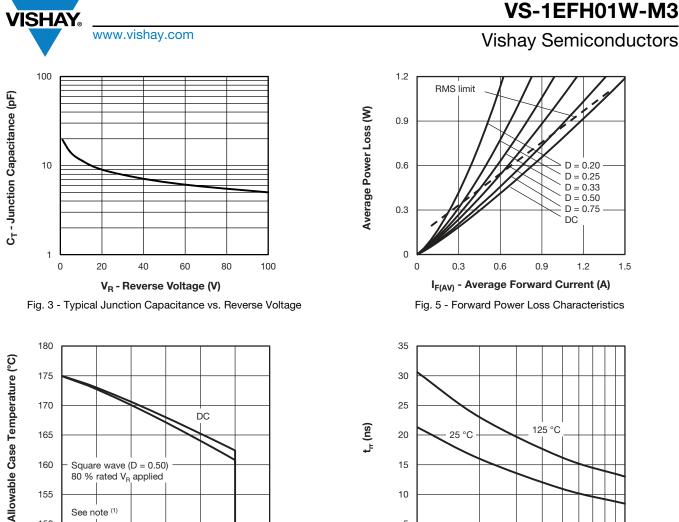


Fig. 1 - Typical Forward Voltage Drop Characteristics





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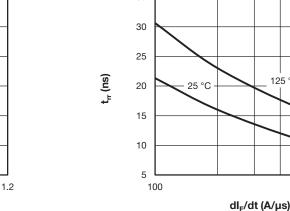


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

D = 0.20D = 0.25 D = 0.33D = 0.50

D = 0.75 DC

1.2

1.5

1000

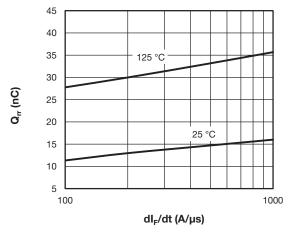


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward Power Loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see Fig. 6); Pd_{REV} = Inverse Power Loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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160

155

150

0

Square wave (D = 0.50) 80 % rated V_R applied

0.4

0.6

I_{F(AV)} - Average Forward Current (A)

Fig. 4 - Maximum Allowable Case Temperature

vs. Average Forward Current

0.8

1

See note (1)

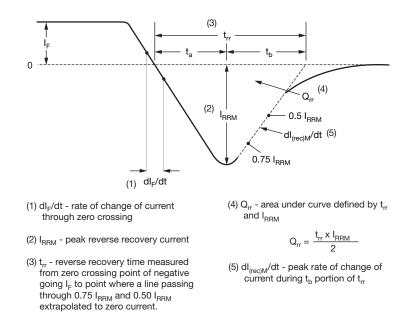
0.2

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Fig. 8 - Reverse Recovery Waveform and Definitions

| ORDERING INFORMATION (Example) | | | | | | |
|--------------------------------|---|--------|-----------------------------------|--|--|--|
| PREFERRED P/N | REFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | |
| VS-1EFH01W-M3-18 | 10 000 | 10 000 | 13"diameter plastic tape and reel | | | |

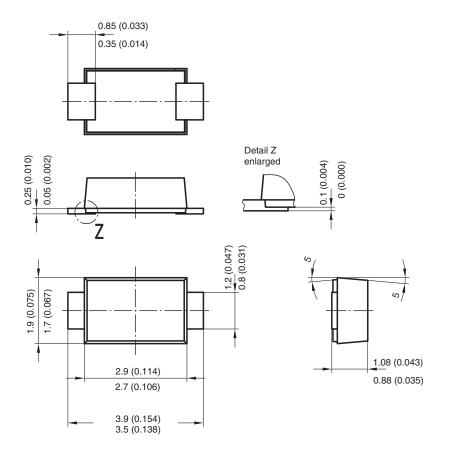
| LINKS TO RELATED DOCUMENTS | | | | |
|----------------------------|--------------------------|--|--|--|
| Dimensions | www.vishay.com/doc?95572 | | | |
| Part marking information | www.vishay.com/doc?95563 | | | |
| Packaging information | www.vishay.com/doc?95577 | | | |



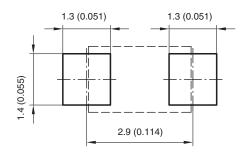
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DO-219AB (SMF)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



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